

TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

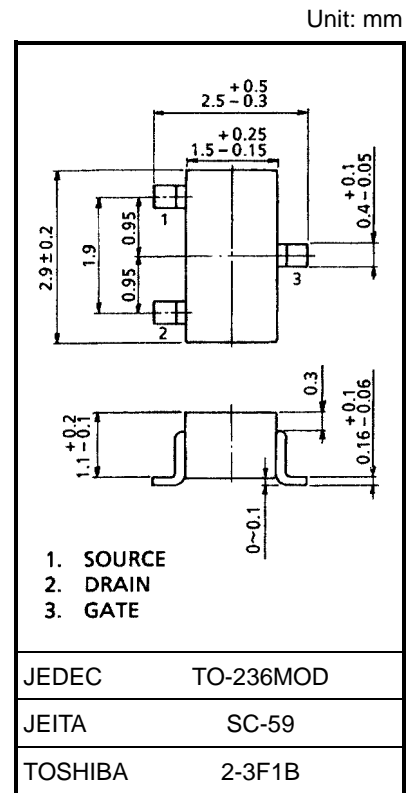
2SK368

Audio Frequency and High Voltage Amplifier Applications
Constant Current Applications

- High breakdown voltage: $V_{GDS} = -100$ V (min)
- High input impedance: $I_{GSS} = -1.0$ nA (max) ($V_{GS} = -80$ V)
- Small package

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V_{GDS}	-100	V
Gate current	I_G	10	mA
Drain power dissipation	P_D	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~125	$^\circ\text{C}$



Weight: 0.012 g (typ.)

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate cut-off current	I_{GSS}	$V_{GS} = -80$ V, $V_{DS} = 0$	—	—	-1.0	nA
Gate-drain breakdown voltage	$V_{(BR) GDS}$	$V_{DS} = 0$, $I_G = -100$ μA	-100	—	—	V
Drain current	I_{DSS} (Note)	$V_{DS} = 10$ V, $V_{GS} = 0$	0.6	—	6.5	mA
Gate-source cut-off voltage	$V_{GS (OFF)}$	$V_{DS} = 10$ V, $I_D = 0.1$ μA	-0.4	—	-3.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10$ V, $V_{GS} = 0$, $f = 1$ kHz	1.5	4.6	—	mS
Input capacitance	C_{iss}	$V_{DS} = 10$ V, $V_{GS} = 0$, $f = 1$ MHz	—	13	—	pF
Reverse transfer capacitance	C_{rss}	$V_{DG} = 10$ V, $I_D = 0$, $f = 1$ MHz	—	3	—	pF
Noise figure	NF	$V_{DS} = 10$ V, $V_{GS} = 0$ $R_G = 100$ k Ω , $f = 100$ Hz	—	0.5	—	dB

Note: I_{DSS} classification O: 0.6~1.4 mA, Y: 1.2~3.0 mA, GR (G): 2.6~6.5 mA

Marking

